AS ENERGI

Thyristor Diode Modules
AMKH 56

V_{RSM} V	V_{RRM}, V_{DRM} V	I_{TRMS} = 95 A (maximum value for continuous operation) I_{TAV} = 55 A (sin 180; T_C = 80 °C)	
700	600	AMKT 56-06E	AMKH 56-06D
900	800	AMKT 56-08E	AMKH 56-08D
1300	1200	AMKT 56-12E	AMKH 56-12E
1500	1400	AMKT 56-14E	AMKH 56-14E
1700	1600	AMKT 56-16E	AMKH 56-16E
1900	1800	AMKT 56-18E	AMKH 56-18E

Symbols and parameters			Values	Units
I_{TAV}	Average on-state current	sin 180; T_C = 85 (100)°C	50 (35)	A
I_D	Direct output current	P3/180; T_a = 45°C; B2/B6 P3/180F; T_a = 35°C; B2/B6	57 / 68 100 / 130	A A
I_{RMS}	Maximum RMS current	P3/180F; T_a =35°C; B2/B6	130 / 3*100	A
I_{TSM}	Surge on-state current	T_{vj} = 25°C; 10 ms T_{vj} = 125°C; 10 ms	1500 1250	A A
I^2t	I^2t value, rating for fusing	T_{vj} = 25°C; 8.3…10 ms T_{vj} = 125°C; 8.3…10 ms	11000 8000	A^2s A^2s
V_T	On-state voltage	T_{vj} = 25°C; I_T =200 A	max. 1.65	V
$V_{T(TO)}$	On-state threshold voltage	T_{vj} = 125°C	0.9	V
r_T	On-state slope resistance	T_{vj} = 125°C	3.5	mΩ
I_{DD} ; I_{RD}	Forward off-state current; Direct reverse current	T_{vj} = 125°C, V_{RD}=V_{RRM}; V_{DD}=V_{DRM}	max. 15	mA
t_{gd}	Gate controlled turn-on delay time	T_{vj} = 25 °C; I_G = 1 A; di_G/dt = 1 A/µs	1	µs
t_{gr}	Gate controlled rise time	V_D = 0,67 * V_{DRM}	2	µs
$(di/dt)_{cr}$	Critical rate of rise of on-state current	T_{vj} = 125°C	max. 150	A/µs
$(dv/dt)_{cr}$	Critical rate of rise of off-state voltage	T_{vj} = 125°C	max. 500 / 1000	V/µs
t_q	Turn-off time	T_{vj} = 125°C	80	µs
I_H	Holding current	T_{vj} = 25°C; typ. / max	150 / 250	mA
I_L	Latching current	T_{vj} = 25°C; R_G=33 Ω; typ. / max	300 / 600	mA
V_{GT}	Gate trigger voltage	T_{vj} = 25°C; d.c.	min. 3	V
I_{GT}	Gate trigger current	T_{vj} = 25°C; d.c.	min. 150	mA
V_{GD}	Gate non-trigger voltage	T_{vj} = 125°C; d.c.	max. 0.25	V
I_{GD}	Gate non-trigger current	T_{vj} = 125°C; d.c.	max. 6	mA
$R_{th(j-c)}$	Thermal resistance, junction to case	cont.; per thyristor/per module	0.57 / 0.29	K/W
		sin.180; per thyristor / per module	0.6 / 0.3	K/W
		rec.120; per thyristor / per module	0.64 / 0.32	K/W
$R_{th(c-s)}$	Thermal resistance, junction to heatsink	per thyristor / per module	0.2 / 0.1	K/W
T_{vj}	Virtual junction temperature		-40 … +125	°C
T_{stg}	Storage temperature range		-40 … +125	°C
V_{ISOL}	Insulation test voltage (r.m.s.)	a.c. 50 Hz; r.m.s.; 1s / 1min.	3600 / 3000	V~
M_S	Mounting torque on heatsink		5 ± 15%	Nm
M_t	Mounting torque for terminals		3 ± 15%	Nm
a	Maximum allowable acceleration		5*9.81	m/s^2
W	Weight	approx.	95	g

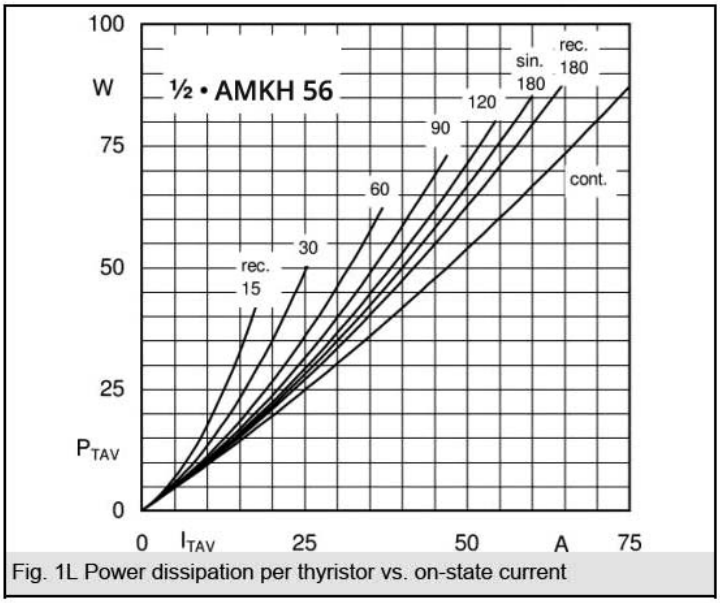


Fig. 1L Power dissipation per thyristor vs. on-state current

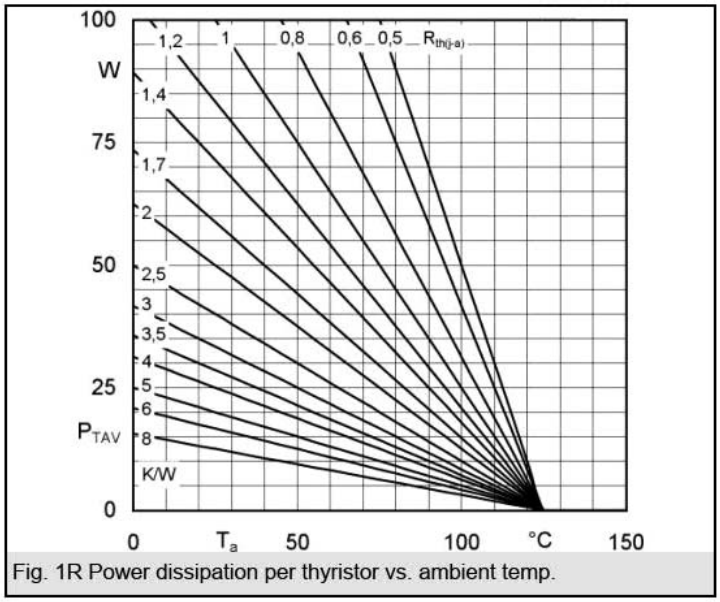


Fig. 1R Power dissipation per thyristor vs. ambient temp.

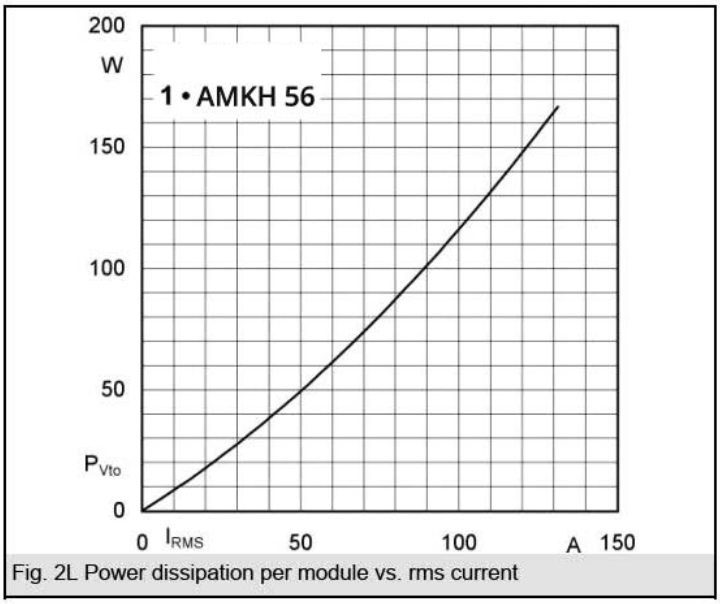


Fig. 2L Power dissipation per module vs. rms current

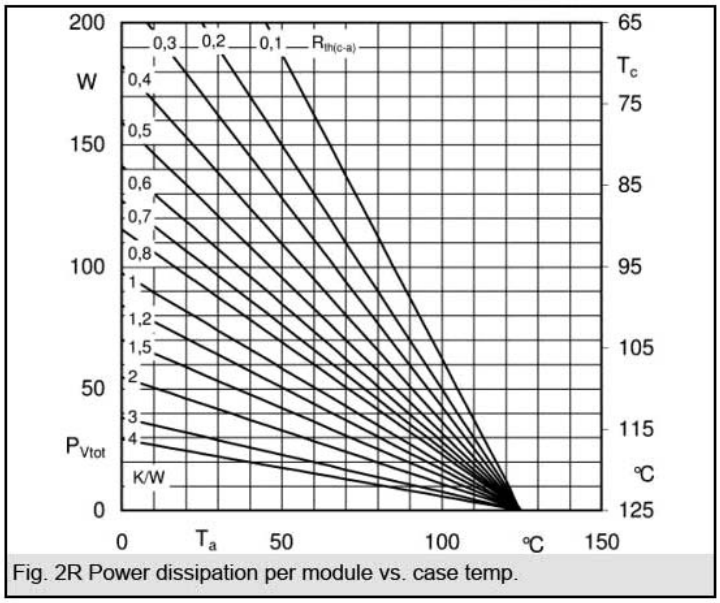


Fig. 2R Power dissipation per module vs. case temp.

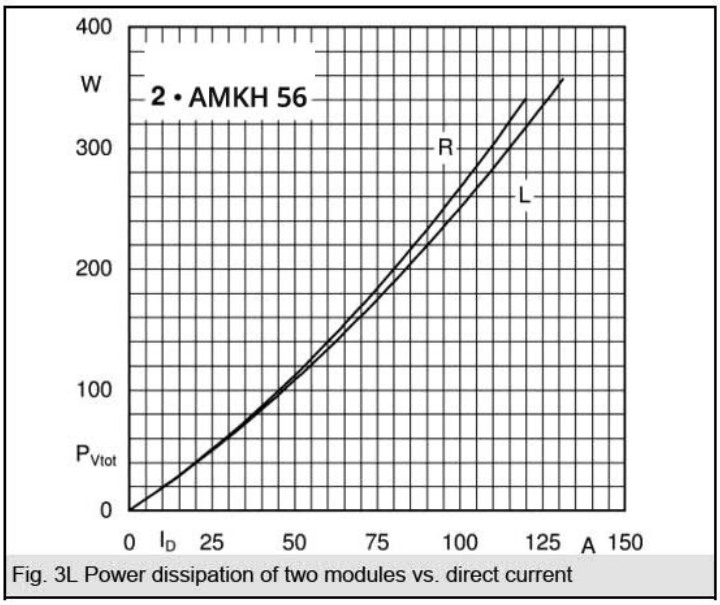


Fig. 3L Power dissipation of two modules vs. direct current

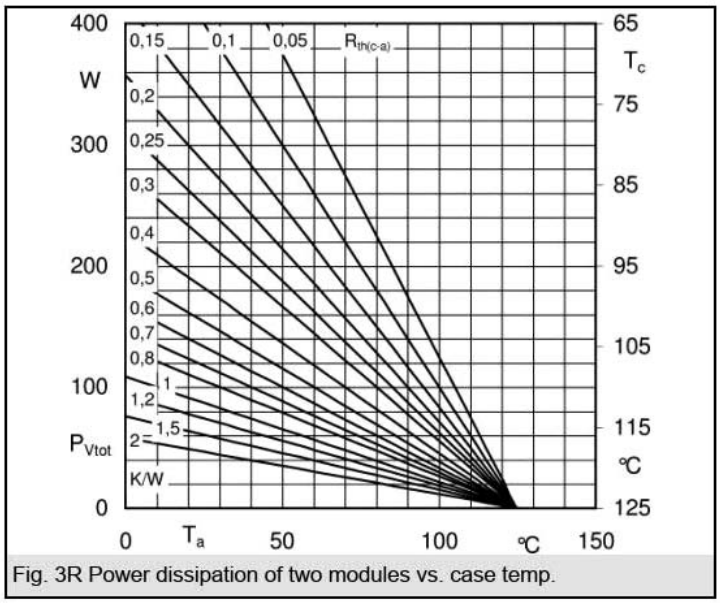


Fig. 3R Power dissipation of two modules vs. case temp.

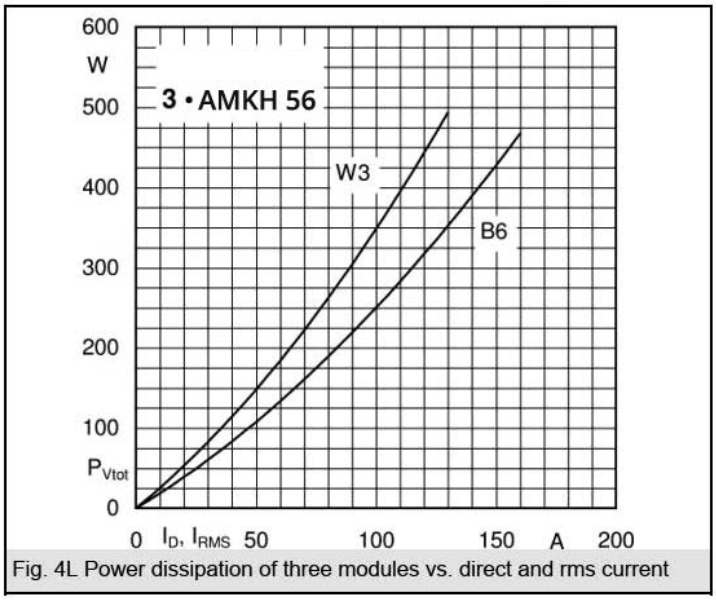


Fig. 4L Power dissipation of three modules vs. direct and rms current

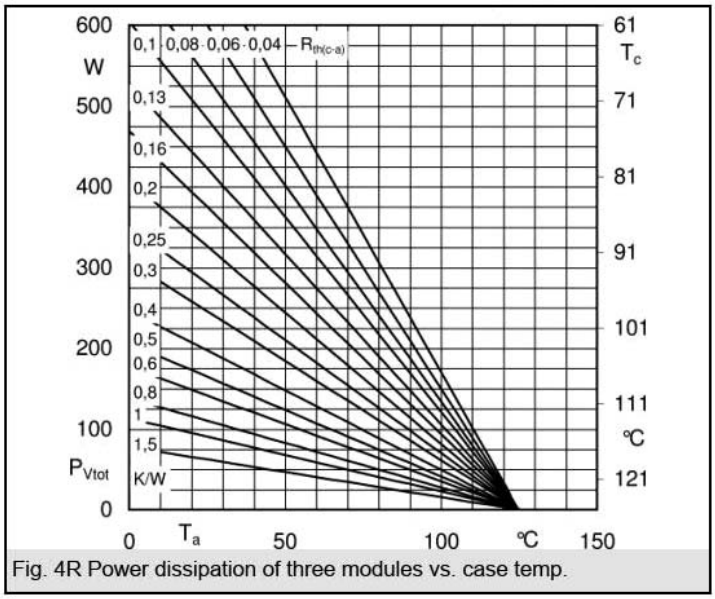


Fig. 4R Power dissipation of three modules vs. case temp.

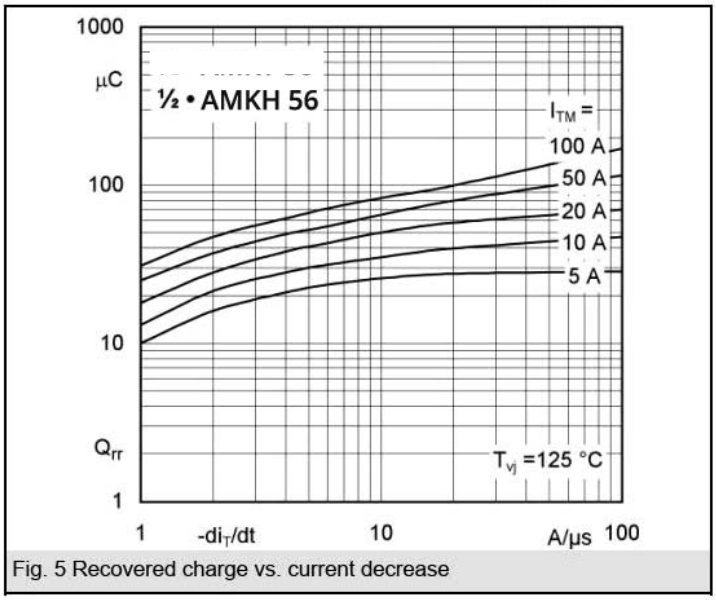


Fig. 5 Recovered charge vs. current decrease

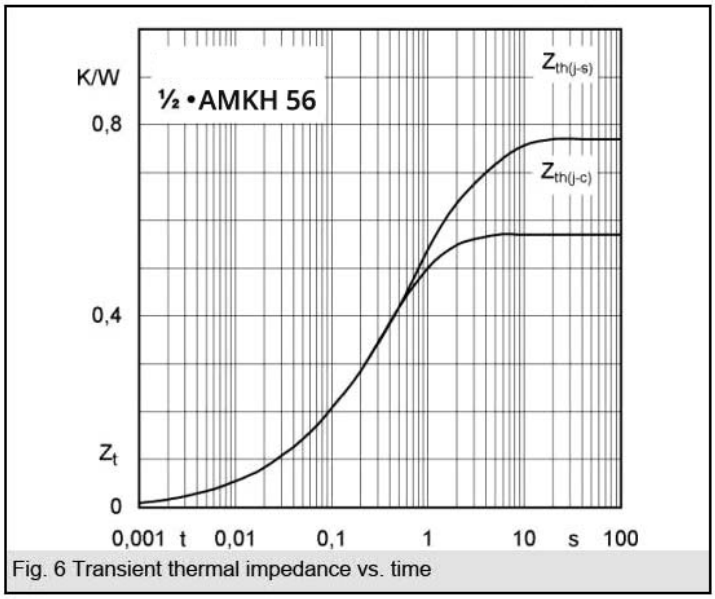


Fig. 6 Transient thermal impedance vs. time

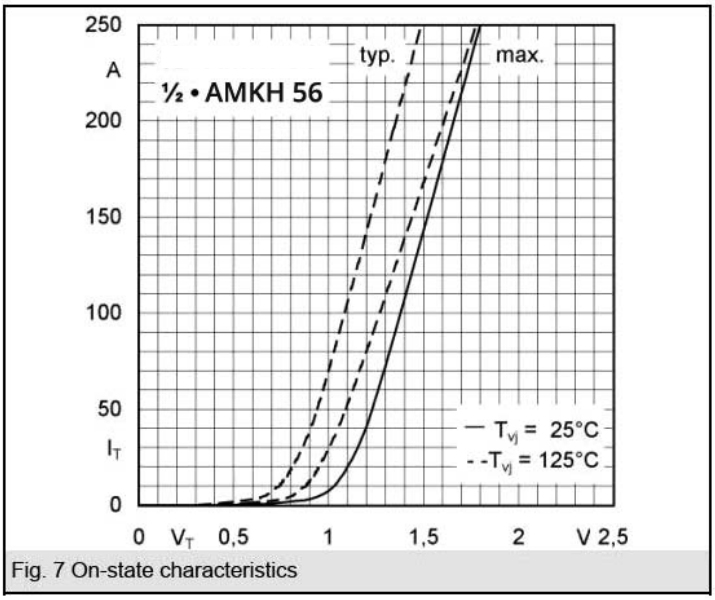


Fig. 7 On-state characteristics

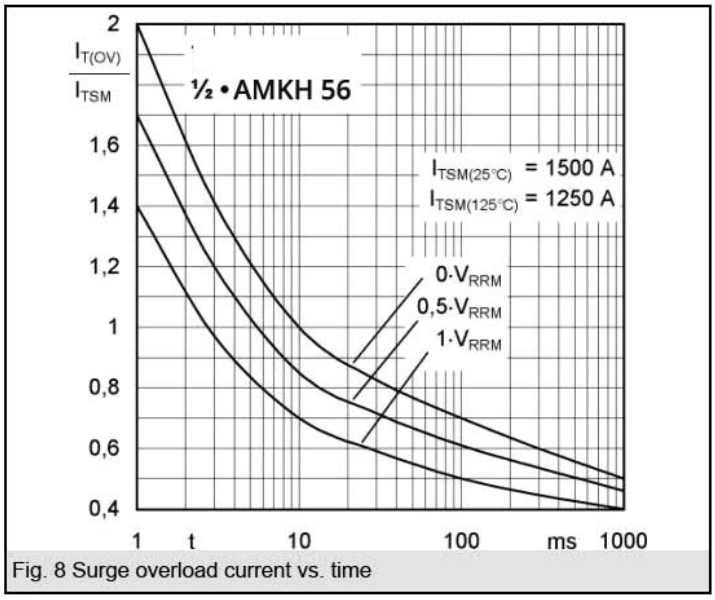


Fig. 8 Surge overload current vs. time

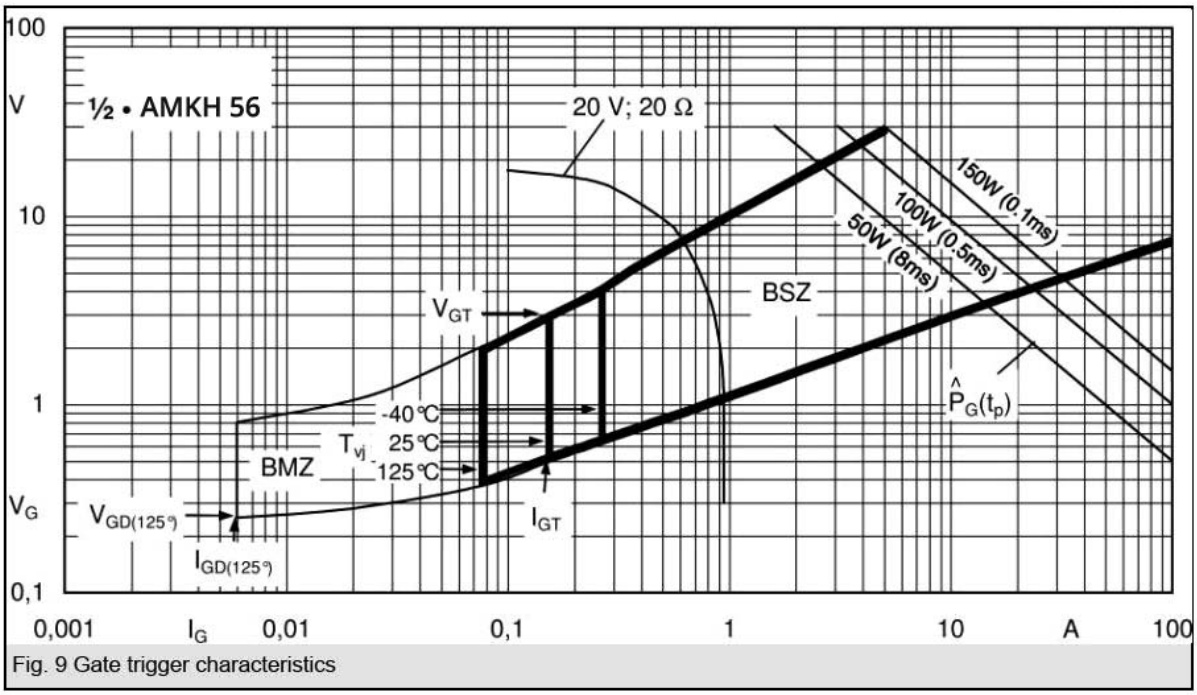
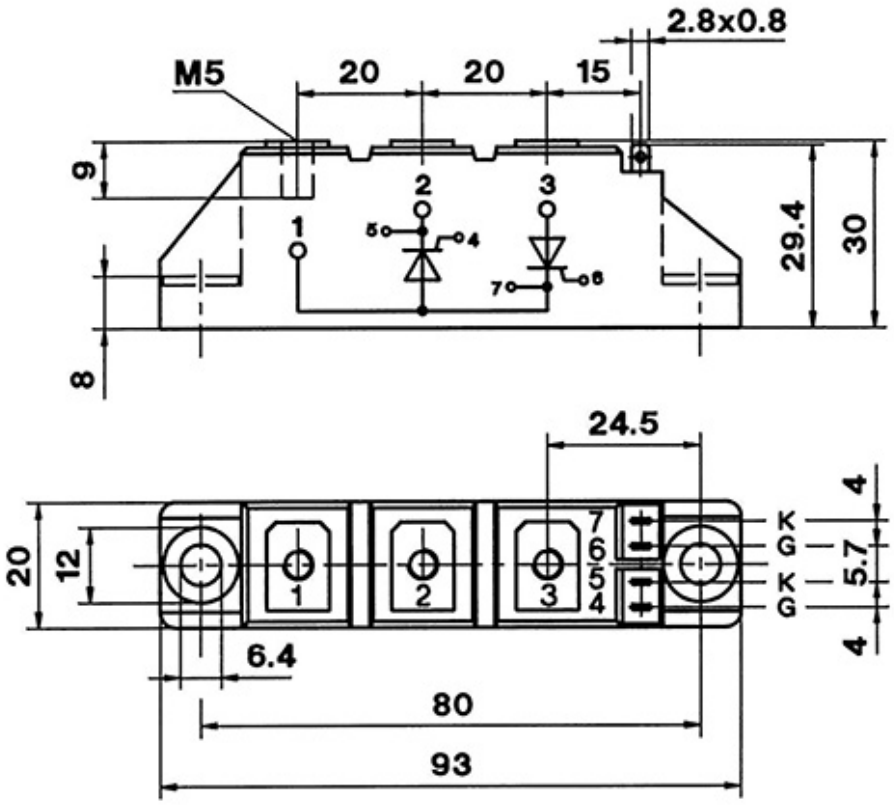


Fig. 9 Gate trigger characteristics

DIMENSIONS

AMKT



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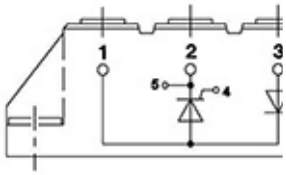

Dimensions in mm

TOPOLOGY OF INTERNAL CONNECTION